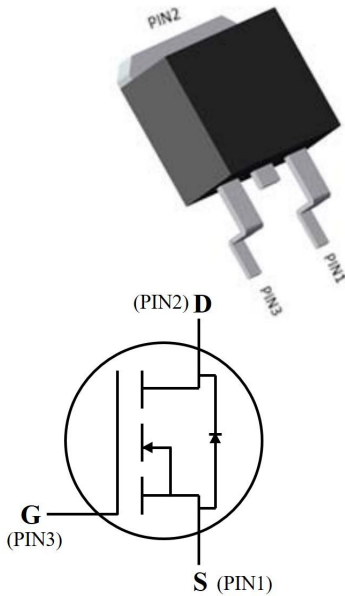


Silicon Carbide Power MOSFET (N-Channel Enhancement)

V_{DS}	1200V
I_D (25°C)	24A
$R_{DS(on)}$	120mΩ



Features

- High speed switching
- Essentially no switching losses
- Reduction of heat sink requirements
- Maximum working temperature at 175 °C
- High blocking voltage
- Fast Intrinsic diode with low recovery current
- High-frequency operation
- Halogen free, RoHS compliant

Typical Applications

Typical applications are in power factor correction(PFC), solar inverter, uninterruptible power supply, motor drives, photovoltaic inverter, electric car and charger.

Mechanical Data

- **Package:** TO-263
- **Terminals:** Tin plated leads
- **Polarity:** As marked

■ Maximum Ratings ($T_c=25^\circ\text{C}$ Unless otherwise specified)

PARAMETER	SYMBOL	UNIT	VALUE	TEST CONDITIONS	NOTE
Device marking code				D2120120BGH	
Drain source voltage @ $T_j=25^\circ\text{C}$	$V_{DS,max}$	V	1200	$V_{GS}=0\text{ V}$, $I_D=100\mu\text{A}$	
Gate source voltage @ $T_j=25^\circ\text{C}$	$V_{GS,max}$	V	-10/+25	Absolute maximum values (AC $f > 1\text{Hz}$, duty cycle $< 1\%$)	Note 1
Gate source voltage @ $T_j=25^\circ\text{C}$	$V_{GS,op}$	V	-5/+20	Recommended operational values	
Continuous drain current @ $T_c=25^\circ\text{C}$	I_D	A	24	$V_{GS}=20\text{V}$, $T_c=25^\circ\text{C}$	Fig.14
Continuous drain current @ $T_c=110^\circ\text{C}$			16.6	$V_{GS}=20\text{V}$, $T_c=110^\circ\text{C}$	
Pulse Drain Current	$I_{D,pulse}$	A	63	Limited by t_{pw}	Fig.15
Avalanche energy, Single Pulse	E_{AS}	mJ	625	$V_{DD}=100\text{V}$, $I_D=7\text{A}$	
Power Dissipation	P_{TOT}	W	161	$T_c=25^\circ\text{C}$, $T_j = 175^\circ\text{C}$	Fig.13
Operating junction and Storage temperature range	T_j, T_{stg}	$^\circ\text{C}$	-55 to +175		
Soldering temperature	T_L	$^\circ\text{C}$	260	1.6mm (0.063") from case for 10s	
Mounting torque	T_M	Nm	0.6	M3 screw Maximum of mounting process: 3	



■Static Electrical Characteristics (Tc=25°C unless otherwise specified)

PARAMETER	SYMBOL	UNIT	Min.	Typ.	Max.	Test Conditions	Note
Gate threshold voltage	$V_{GS(th)}$	V		2.95		$V_{DS}=V_{GS}$, $I_D=10mA$	Fig.4, 11
Drain source breakdown voltage	$V_{(BR)DSS}$	V	1200			$V_{GS}=0$, $I_D=100\mu A$	
Zero gate voltage drain current	I_{DSS}	μA		<1	50	$V_{DS}=1200V$, $V_{GS}=0V$	
				10	500	$V_{DS}=1200V$, $V_{GS}=0V$, $T_j=175^\circ C$	
Gate source leakage current	I_{GSS}	nA			250	$V_{GS}=20V$, $V_{DS}=0V$	
Current drain source on-state resistance	$R_{DS(on)}$	$m\Omega$		120	160	$V_{GS}=20V$, $I_D=10A$	Fig.3, 5, 6
				200		$V_{GS}=20V$, $I_D=10A$, $T_j=175^\circ C$	
Transconductance	g_f	S		6.2		$V_{DS}=12.5V$, $I_D=20A$	

■Dynamic Electrical Characteristics (Tc=25°C unless otherwise specified)

PARAMETER	SYMBOL	UNIT	Min.	Typ.	Max.	Test Conditions	Note
Input capacitance	C_{iss}	pF		1083		$V_{DS}=800V$, $V_{GS}=0V$, $T_j=25^\circ C$, $f=1MHz$, $V_{AC}=25mV$	Fig.10
Output capacitance	C_{oss}			56			
Reverse capacitance	C_{rss}			8			
Coss stored energy	E_{oss}	μJ		23			Fig.12
Gate source charge	Q_{gs}	nC		14.5		$V_{DS}=800V$, $V_{GS}=-5/20V$, $I_D=10A$	Fig.16
Gate drain charge	Q_{gd}			29			
Gate charge	Q_g			67			
Internal Gate Resistance	$R_{G(int)}$	Ω		1.8		$f=1MHz$, $V_{AC}=25mV$	

■Switching Characteristics (Tc=25°C unless otherwise specified)

PARAMETER	SYMBOL	UNIT	Min.	Typ.	Max.	Test Conditions	Note
Turn on delay time	$t_{d(on)}$	ns		24		$V_{DD}=800V$, $V_{GS}=0/+20V$, $I_D=8A$, $R_L=100\Omega$, $R_{G(ext)}=10\Omega$	
Rise time	t_r			24			
Turn off delay time	$t_{d(off)}$			34			
Fall time	t_f			33			
Turn on switching energy	E_{on}	μJ		13		$V_{DD}=800V$, $V_{GS}=0/+20V$, $I_D=10A$, $R_{g(ext)}=2.7\Omega$	Fig.17, 18
Turn off switching energy	E_{off}			19			



■Body diode characteristics (Tc=25°C unless otherwise specified)

PARAMETER	SYMBOL	UNIT	Min.	Typ.	Max.	Test Conditions	Note
Diode forward voltage	V _{SD}	V		3.4		V _{GS} =0V, I _{SD} =2.5A	Fig.8
Continuous diode forward current	I _s	A		24.5		V _{GS} =0V, Tc=25°C	
Reverse recovery time	t _{rr}	nS		53		V _{DS} =400V, V _{GS} =0V, I _{SD} =10A, di/dt=300A/uS	
Reverse recovery charge	Q _{rr}	nC		63			
Peak reverse recovery current	I _{rrm}	A		2.25			

Note 1: When using SiC Body Diode the maximum recommended V_{GS} = -5V

■Thermal Characteristics (T_a=25°C Unless otherwise specified)

PARAMETER	SYMBOL	UNIT	Value
Thermal resistance	R _{θJ-C}	°C/W	0.93

■Typical Characteristics

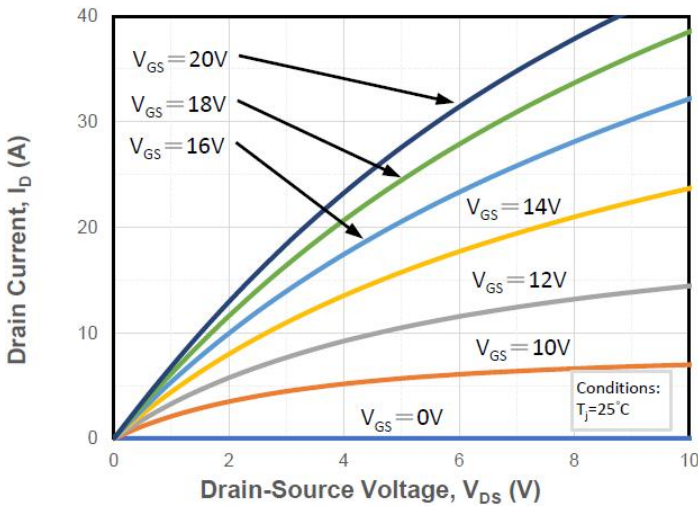


Figure 1. Output Characteristics Tj = 25°C

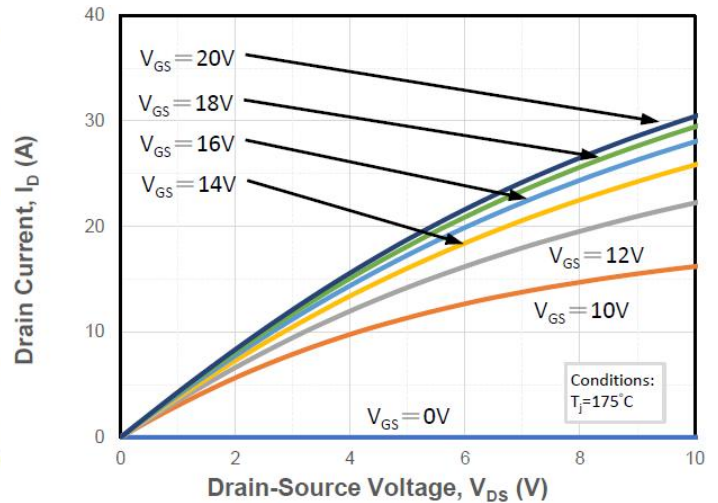


Figure2. Output Characteristics Tj = 175°C

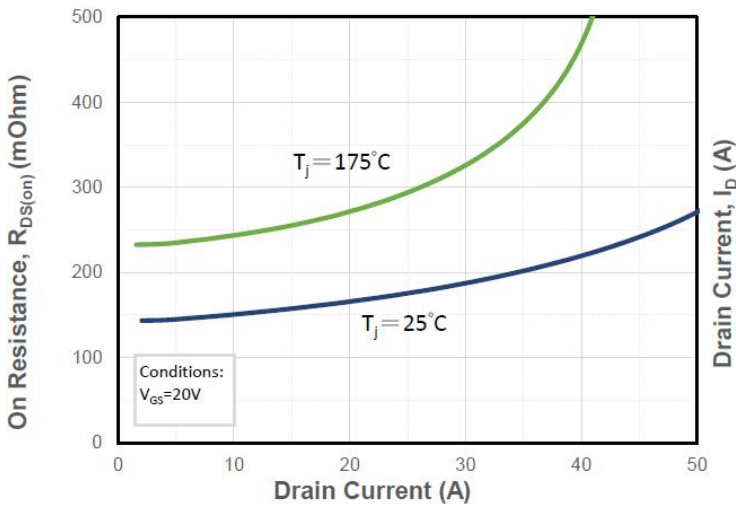


Figure 3. On-resistance vs. drain current

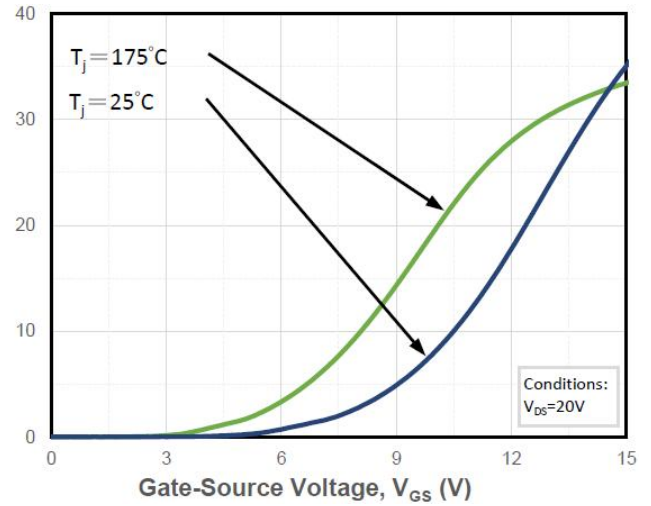


Figure 4. Transfer Characteristics for various Tj

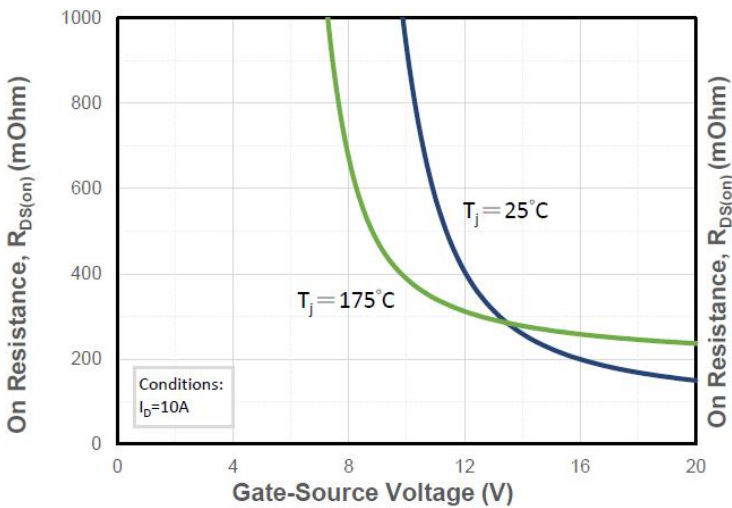


Figure 5. On-resistance vs. gate voltage for various Tj

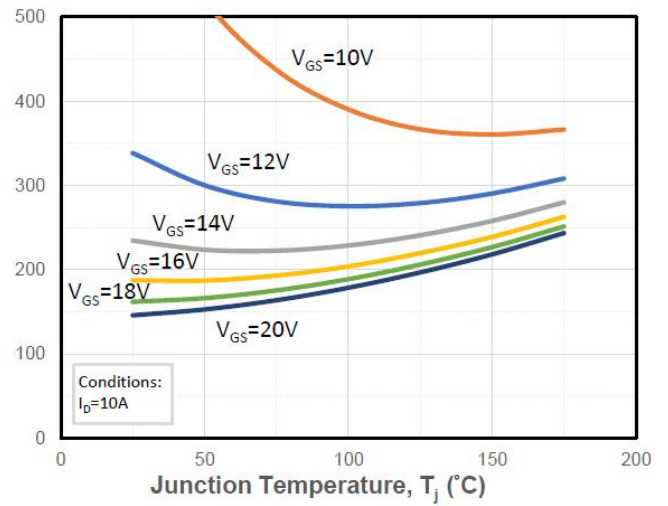


Figure 6. On-resistance vs. Temperature for various Gate voltage

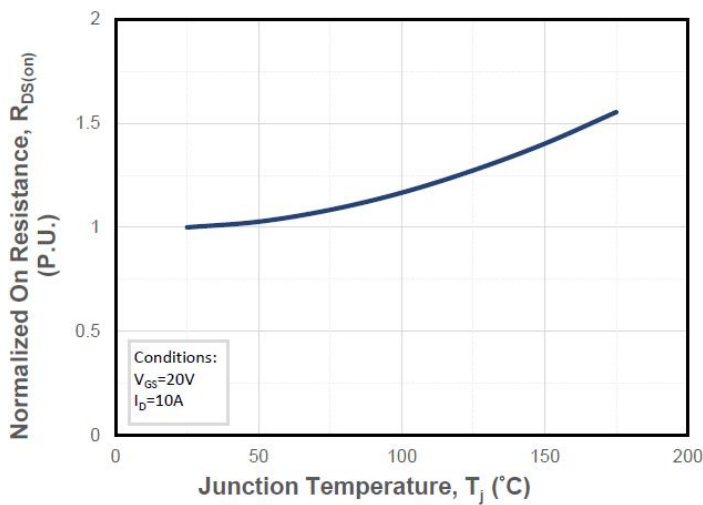


Figure 7. Normalized On-Resistance vs. Temperature

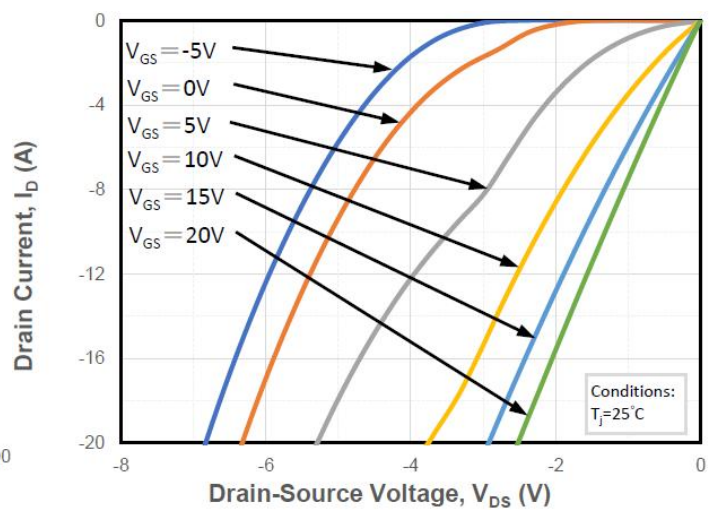


Figure 8. Reverse Output Characteristics at Tj = 25°C

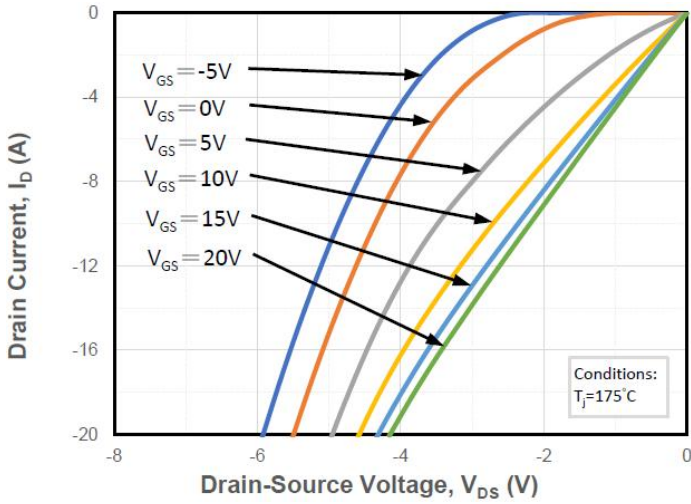


Figure 9. Reverse Output Characteristics at $T_j = 175^\circ\text{C}$

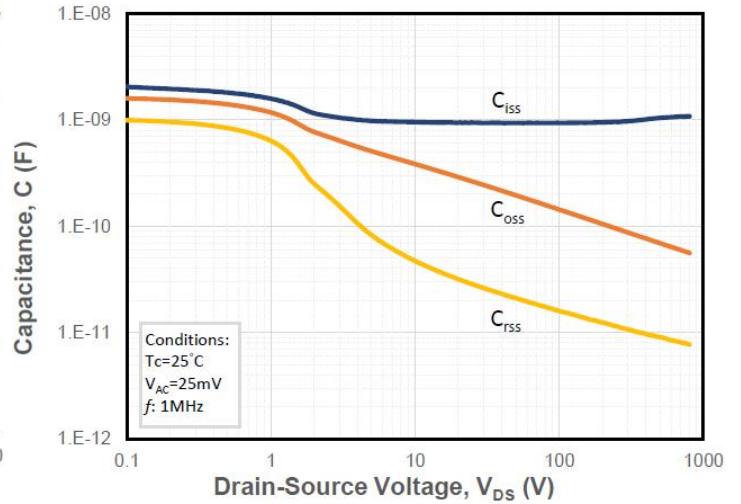


Figure 10. Capacitances vs. Drain to Source Voltage

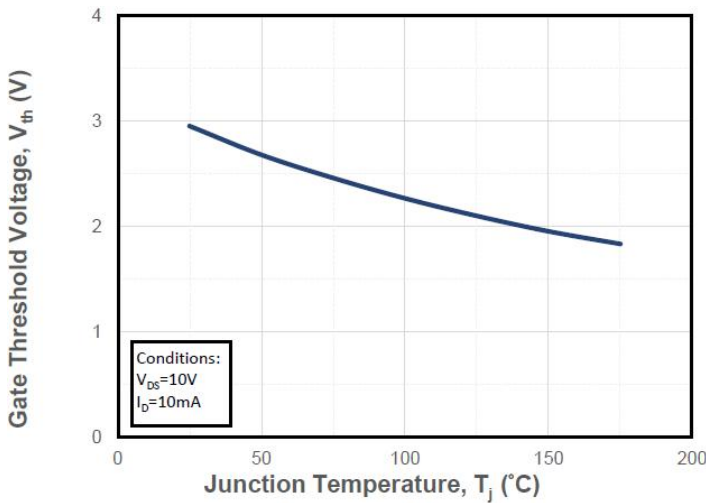


Figure 11. Threshold voltage vs. temperature

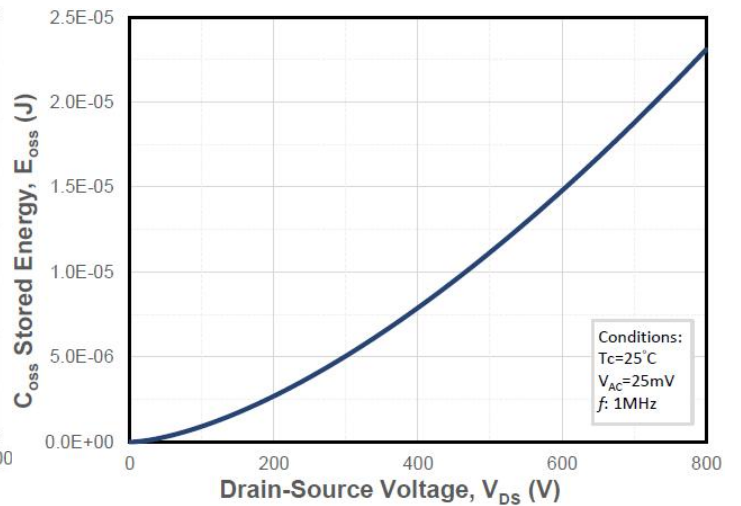


Figure 12. Output Capacitor Stored Energy

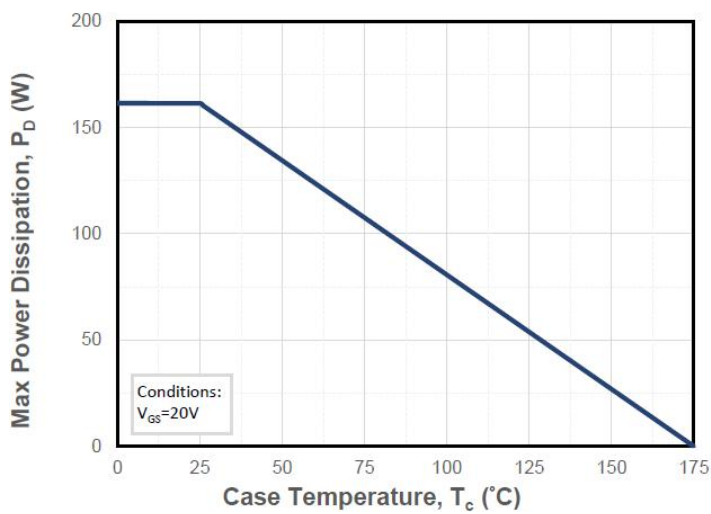


Figure 13. Maximum Power Dissipation Derating vs. Case Temperature

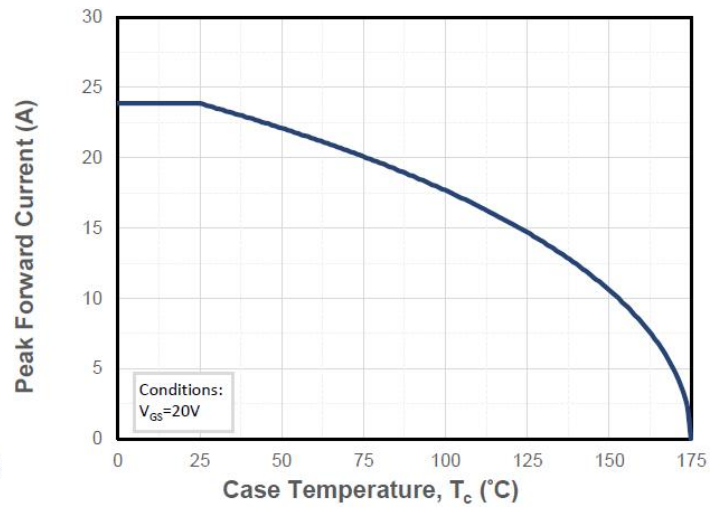


Figure 14. Drain Current Derating vs. Case Temperature

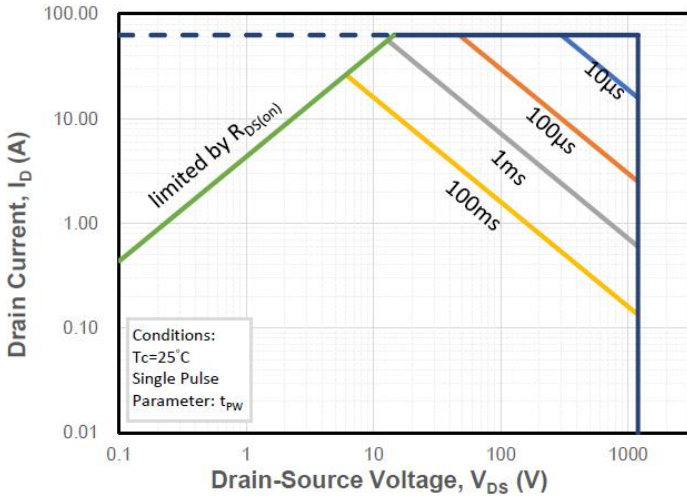


Figure 15. Safe Operating Area

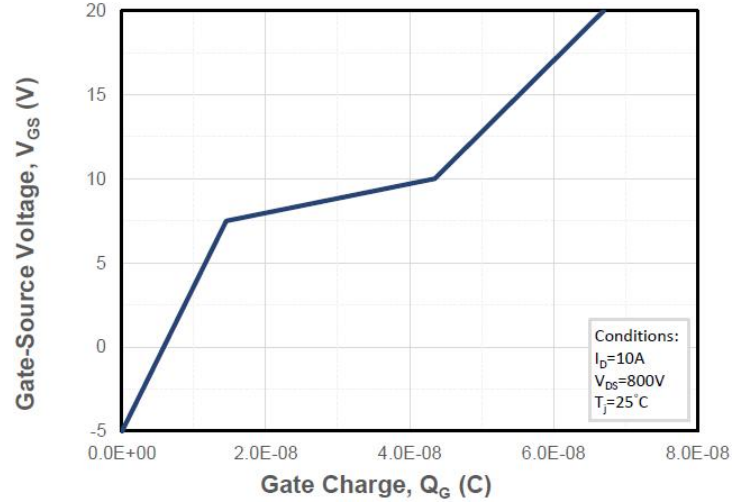


Figure 16. Gate Charge Characteristics

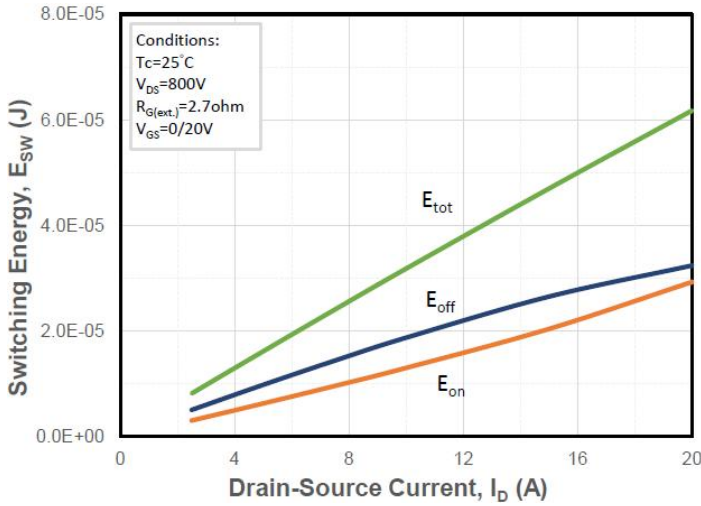


Figure 17. Clamped Inductive Switching Energy vs. Drain Current

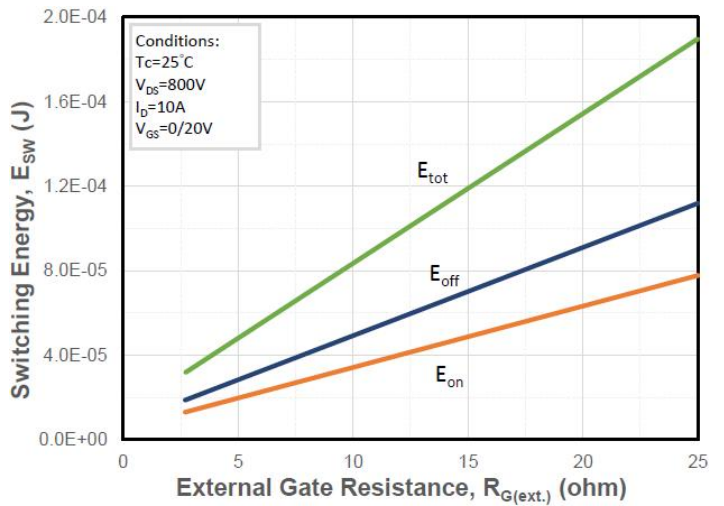


Figure 18. Clamped Inductive Switching Energy vs. External Gate Resistor ($R_{G(ext.)}$)

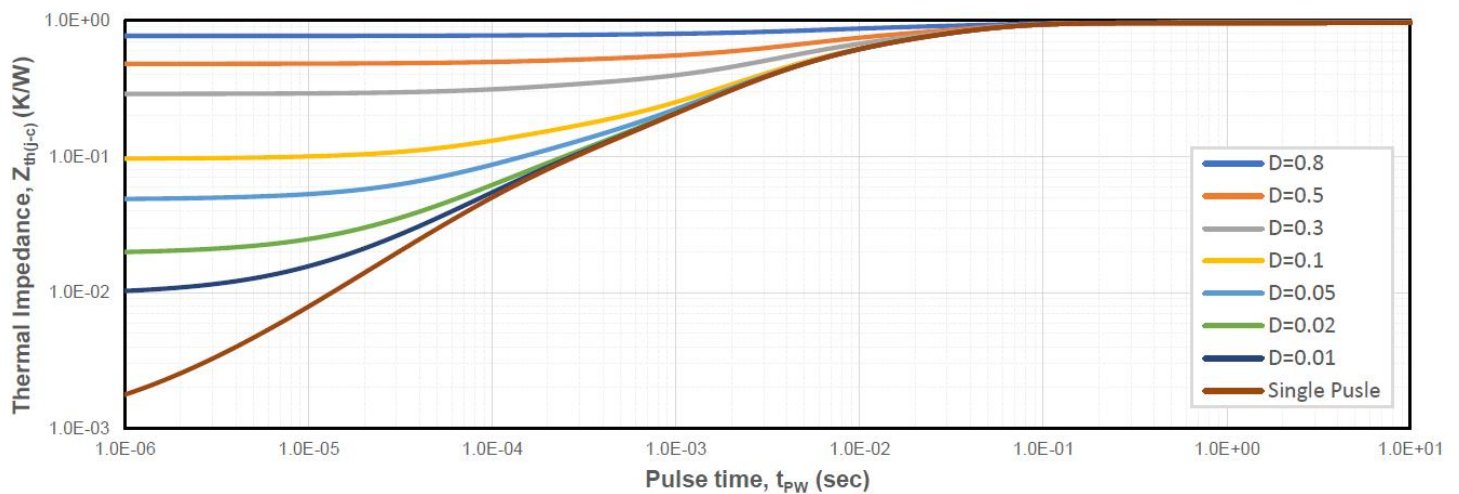


Figure 19. Transient Junction to Case Thermal Impedance

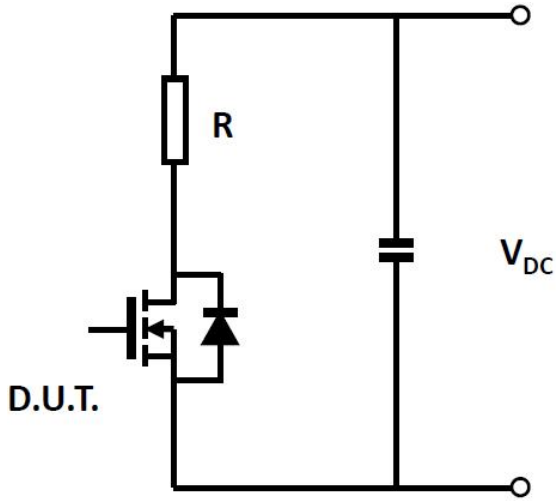


Figure 20. Schematic of Resistive Switching

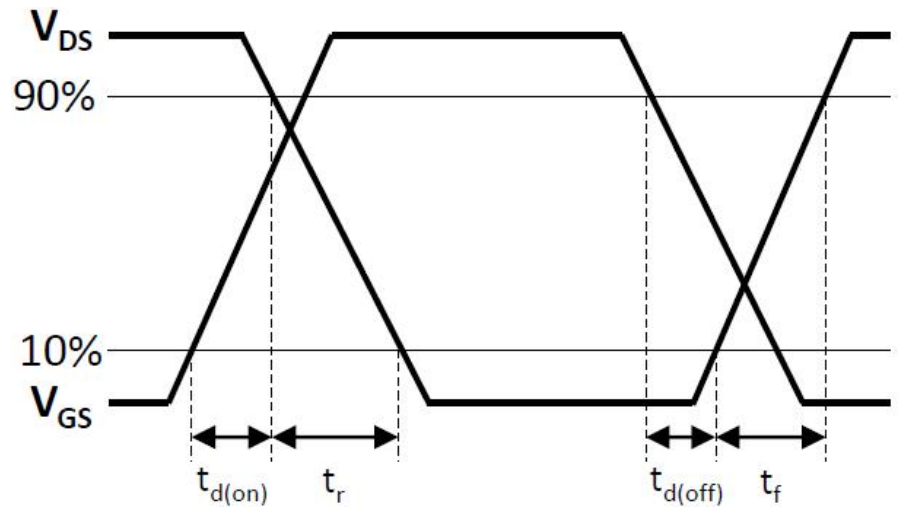
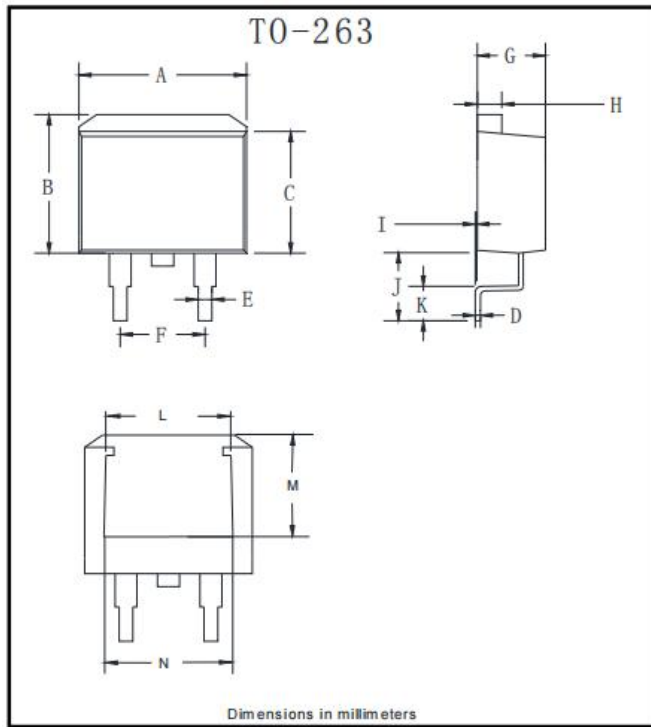


Figure 21. Switching Times Definition

■Outline Dimensions



TO-263		
Dim	Min	Max
A	9.5	11.5
B	9.7	10.5
C	8.4	9.0
D	0.28	0.64
E	0.68	0.94
F	4.55	5.6
G	4.04	5.10
H	1.14	1.4
I	0	0.2
J	4.9	6.05
K	1.79	2.79
L	7.3	7.9
M	6.2	6.8
N	7.6	8.2



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